

STARPOWER

SEMICONDUCTOR

IGBT

GD600SGU120C2S

1200V/600A 1 in one-package

General Description

STARPOWER IGBT Power Module provides ultrafast switching speed as well as short circuit ruggedness. It's designed for the applications such as electronic welder and inductive heating.

Features

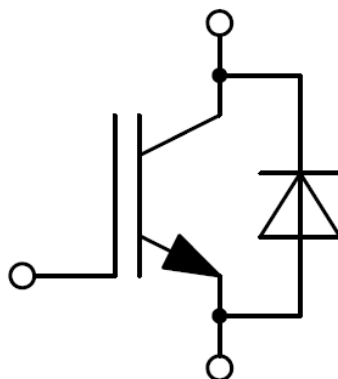
- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- Rugged with ultrafast performance
- $V_{CE(sat)}$ with positive temperature coefficient
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Switching mode power supply
- Inductive heating
- Electronic welder

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	1200	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=70^{\circ}\text{C}$	830 600	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	1200	A
P_D	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	4032	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	600	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	1200	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	150	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V

IGBT Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		2.90	3.35	V
		$I_C=600\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		3.60		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=6.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.0	5.8	6.6	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			0.25		Ω
C_{ies}	Input Capacitance			39.0		nF
C_{res}	Reverse Transfer Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		2.55		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		6.30		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.1\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		205		ns
t_r	Rise Time			50		ns
$t_{d(off)}$	Turn-Off Delay Time			265		ns
t_f	Fall Time			140		ns
E_{on}	Turn-On Switching Loss			50.4		mJ
E_{off}	Turn-Off Switching Loss			20.0		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=600\text{A}, R_G=1.1\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		210		ns
t_r	Rise Time			55		ns
$t_{d(off)}$	Turn-Off Delay Time			275		ns
t_f	Fall Time			175		ns
E_{on}	Turn-On Switching Loss			66.0		mJ
E_{off}	Turn-Off Switching Loss			28.9		mJ
I_{SC}	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		3900		A

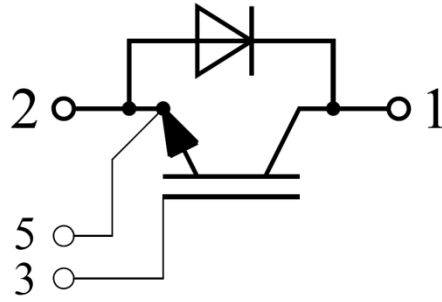
Diode Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		2.25	2.70	V
		$I_F=600\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.35		
Q_r	Recovered Charge	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=12\text{kA}/\mu\text{s}, V_{GE}=\pm 15\text{V},$ $T_j=25^\circ\text{C}$		42.0		μC
I_{RM}	Peak Reverse Recovery Current			492		A
E_{rec}	Reverse Recovery Energy			16.6		mJ
Q_r	Recovered Charge			80.4		μC
I_{RM}	Peak Reverse Recovery Current	$V_{CC}=600\text{V}, I_F=600\text{A},$ $-di/dt=12\text{kA}/\mu\text{s}, V_{GE}=\pm 15\text{V},$ $T_j=125^\circ\text{C}$		672		A
E_{rec}	Reverse Recovery Energy			37.9		mJ

Module Characteristics $T_c=25^\circ\text{C}$ unless otherwise noted

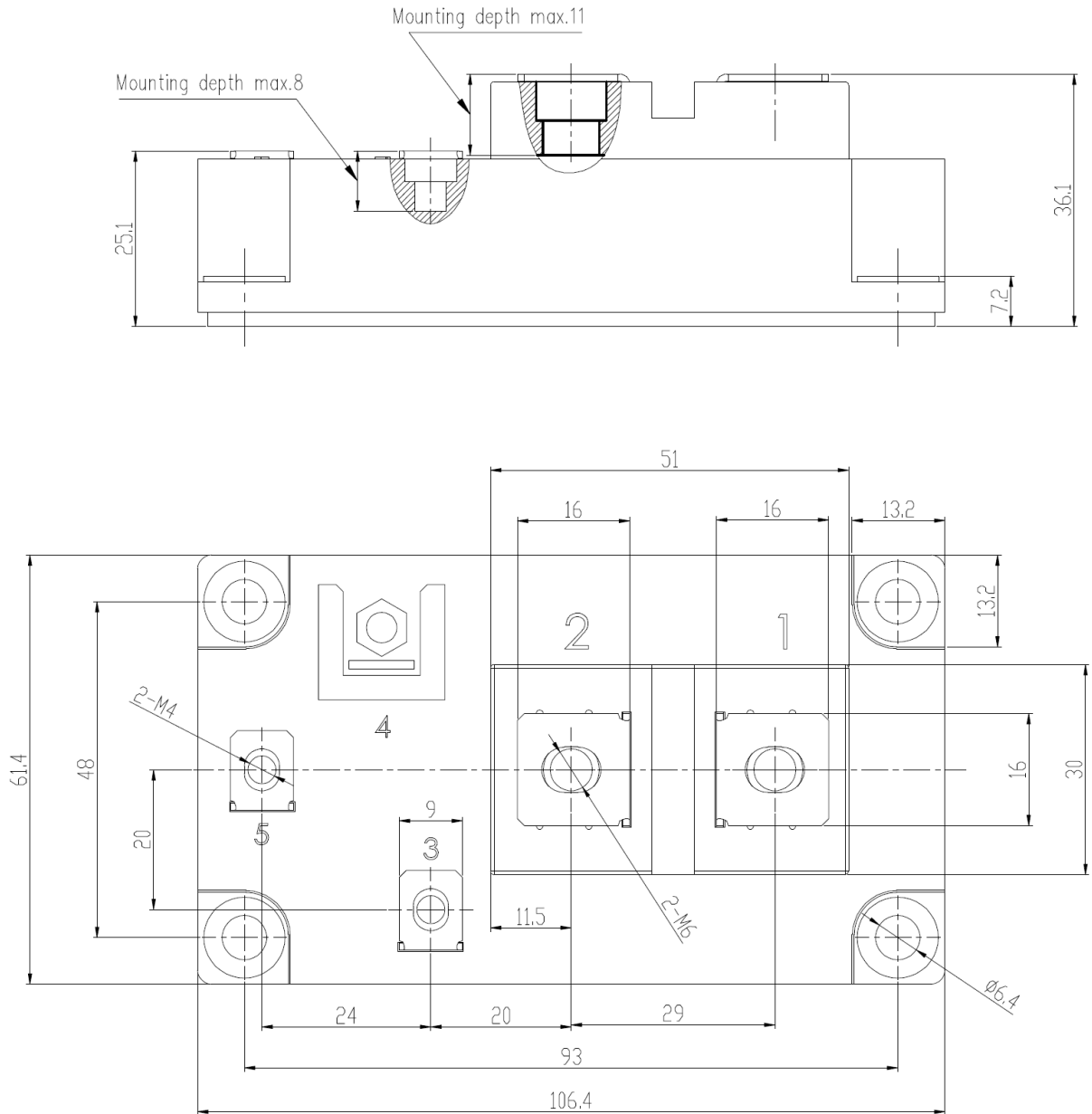
Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.18		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.031	K/W
	Junction-to-Case (per Diode)			0.070	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.051		K/W
	Case-to-Heatsink (per Diode)		0.114		
	Case-to-Heatsink (per Module)		0.035		
M	Terminal Connection Torque, Screw M4	1.1		2.0	N.m
	Terminal Connection Torque, Screw M6	2.5		5.0	
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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